



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



BUJD203AX

NPN power transistor with integrated diode

Rev. 01 — 27 September 2010

Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT186A (TO220F) full pack plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Isolated package
- Very low switching and conduction losses

1.3 Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

1.4 Quick reference data

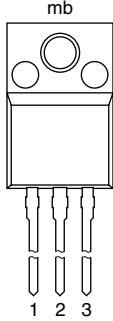
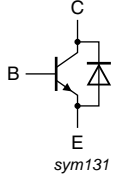
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	see Figure 1 ; see Figure 2 ; DC; see Figure 4	-	-	4	A
P_{tot}	total power dissipation	$T_h \leq 25\text{ °C}$; see Figure 3	-	-	26	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	850	V
Static characteristics						
h_{FE}	DC current gain	$I_C = 500\text{ mA}$; $V_{CE} = 5\text{ V}$; see Figure 11 ; $T_h = 25\text{ °C}$	13	21	32	
		$V_{CE} = 5\text{ V}$; $I_C = 3\text{ A}$; see Figure 11 ; $T_h = 25\text{ °C}$	-	12.5	-	
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0\text{ A}$; $L_C = 25\text{ mH}$; $I_C = 10\text{ mA}$; see Figure 6 ; see Figure 7	400	450	-	V



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	C	collector		
3	E	emitter		
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

3. Ordering information

Table 3. Ordering information

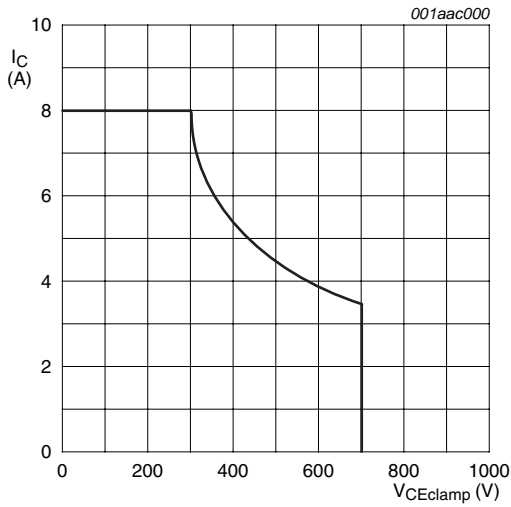
Type number	Package		
	Name	Description	Version
BUJD203AX	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

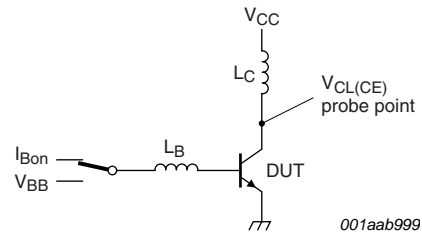
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	850	V
V_{CBO}	collector-base voltage	$I_E = 0\text{ A}$	-	850	V
V_{CEO}	collector-emitter voltage	$I_B = 0\text{ A}$	-	425	V
I_C	collector current	DC; see Figure 1 ; see Figure 2 ; see Figure 4	-	4	A
I_{CM}	peak collector current	see Figure 1 ; see Figure 2 ; see Figure 4	-	8	A
I_B	base current	DC	-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	$T_h \leq 25\text{ °C}$; see Figure 3	-	26	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C



$$T_j \leq T_{j(max)} \text{ } ^\circ\text{C}$$

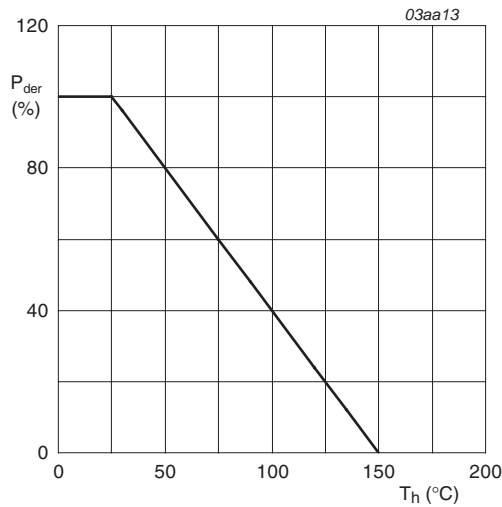
Fig 1. Reverse bias safe operating area



$$V_{CL(CE)} \leq 1000 \text{ V}; V_{CC} = 150 \text{ V}; V_{BB} = -5 \text{ V};$$

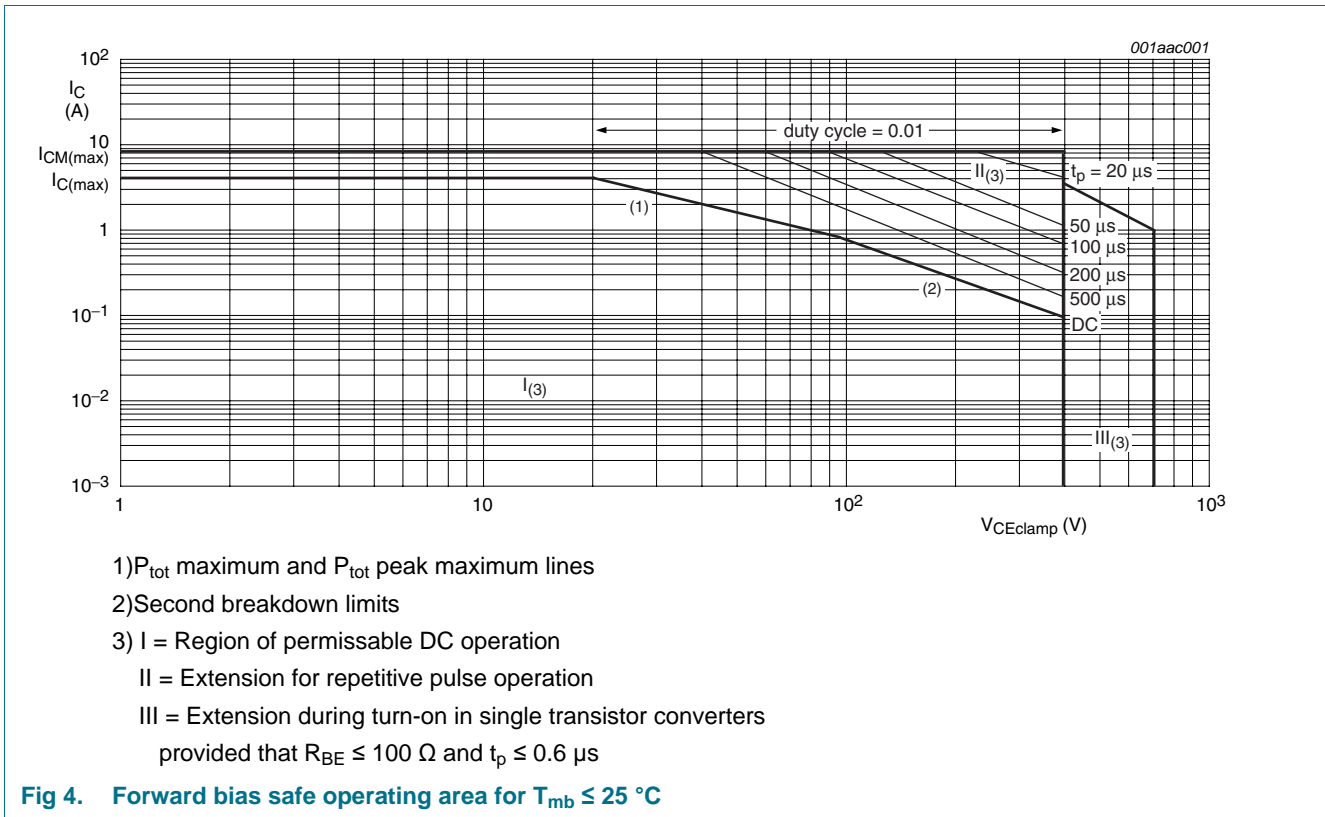
$$L_B = 1 \mu\text{H}; L_C = 200 \mu\text{H}$$

Fig 2. Test circuit for reverse bias safe operating area



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

Fig 3. Normalized total power dissipation as a function of heatsink temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 5	-	-	4.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

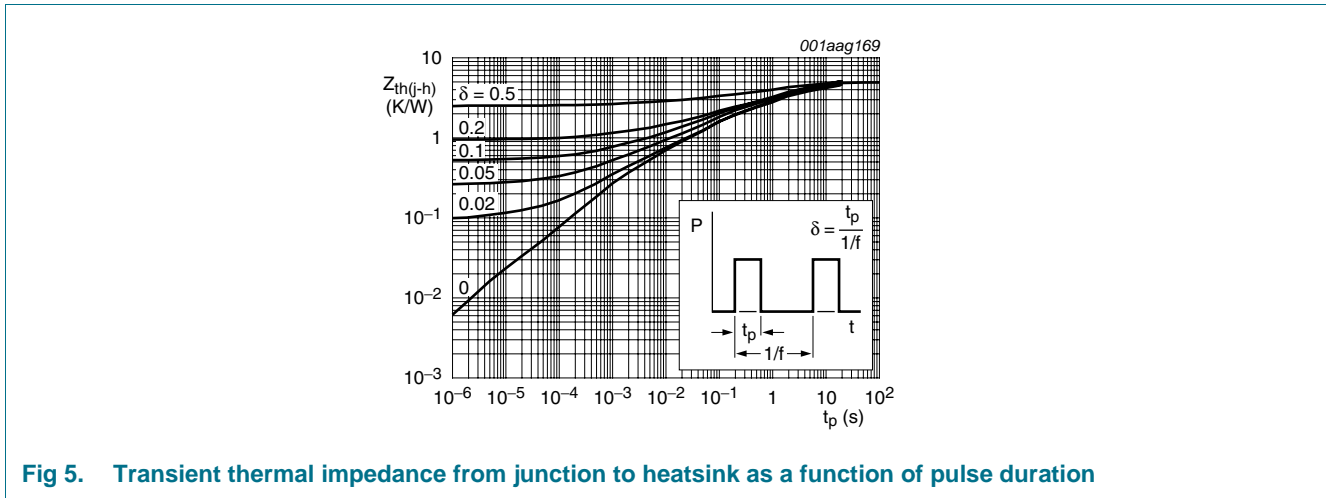


Fig 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	$50 \text{ Hz} \leq f \leq 60 \text{ Hz}$; $RH \leq 65 \%$; $T_h = 25 \text{ }^\circ\text{C}$; from all terminals to external heatsink; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	$T_h = 25 \text{ }^\circ\text{C}$; $f = 1 \text{ MHz}$; from collector to external heatsink	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = 850\text{ V}; T_j = 125\text{ }^\circ\text{C}$	[1]	-	2	mA
		$V_{BE} = 0\text{ V}; V_{CE} = 850\text{ V}; T_j = 25\text{ }^\circ\text{C}$	[1]	-	1	mA
I_{CBO}	collector-base cut-off current	$V_{CB} = 850\text{ V}; I_E = 0\text{ A}$	[1]	-	1	mA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 425\text{ V}; I_B = 0\text{ A}$	[1]	-	0.1	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 7\text{ V}; I_C = 0\text{ A}$	-	-	10	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA}; L_C = 25\text{ mH};$ see Figure 6 ; see Figure 7	400	450	-	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 3\text{ A}; I_B = 0.6\text{ A};$ see Figure 8 ; see Figure 9	-	0.29	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3\text{ A}; I_B = 0.6\text{ A};$ see Figure 10	-	0.99	1.5	V
V_F	forward voltage	$I_F = 2\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	1.04	1.5	V
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}; T_h = 25\text{ }^\circ\text{C};$ see Figure 11	10	15	32	
		$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; T_h = 25\text{ }^\circ\text{C};$ see Figure 11	13	21	32	
		$I_C = 2\text{ A}; V_{CE} = 5\text{ V}; T_h = 25\text{ }^\circ\text{C};$ see Figure 11	11	16	22	
		$I_C = 3\text{ A}; V_{CE} = 5\text{ V}; T_h = 25\text{ }^\circ\text{C};$ see Figure 11	-	12.5	-	
Dynamic characteristics						
t_{on}	turn-on time	$I_C = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; I_{Boff} = -0.5\text{ A};$ $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C};$ resistive load; see Figure 12 ; see Figure 13	-	0.52	0.6	μs
t_s	storage time	$I_C = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; I_{Boff} = -0.5\text{ A};$ $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C};$ resistive load; see Figure 12 ; see Figure 13	-	2.7	3.3	μs
		$I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 25\text{ }^\circ\text{C};$ inductive load; see Figure 14 ; see Figure 15	-	1.2	1.4	μs
		$I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C};$ inductive load; see Figure 14 ; see Figure 15	-	-	1.8	μs
t_f	fall time	$I_C = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; I_{Boff} = -0.5\text{ A};$ $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C};$ resistive load; see Figure 12 ; see Figure 13	-	0.3	0.35	μs
		$I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C};$ inductive load; see Figure 14 ; see Figure 15	-	-	0.12	μs
		$I_C = 2\text{ A}; I_{Bon} = 0.4\text{ A}; V_{BB} = -5\text{ V};$ $L_B = 1\text{ }\mu\text{H}; T_j = 25\text{ }^\circ\text{C};$ inductive load; see Figure 14 ; see Figure 15	-	0.03	0.06	μs

[1] Measured with half-sine wave voltage (curve tracer)

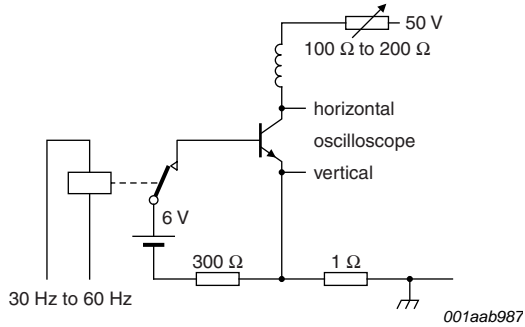


Fig 6. Test circuit for collector-emitter sustaining voltage

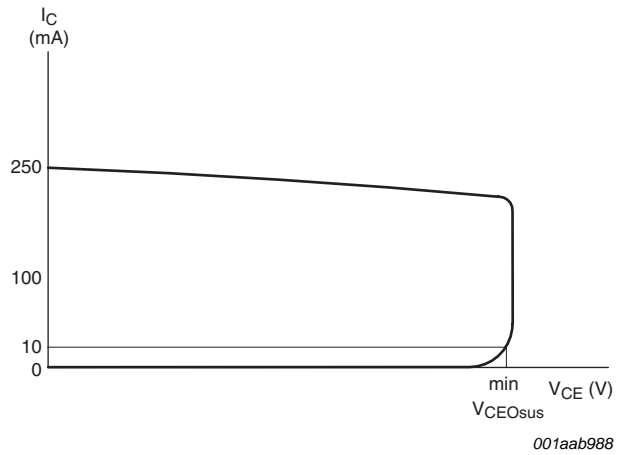


Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform

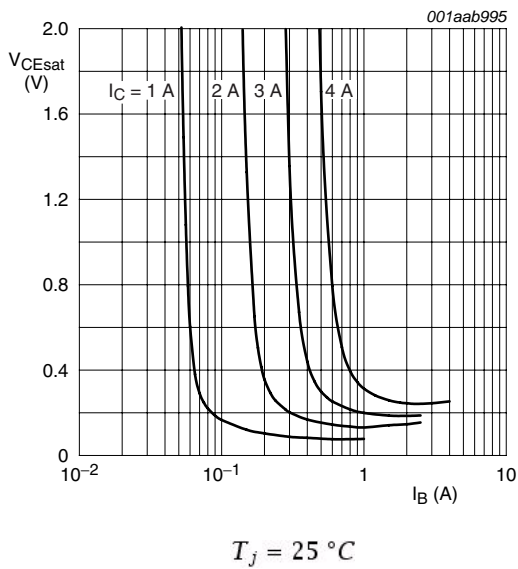


Fig 8. Collector-emitter saturation voltage as a function of base current; typical values

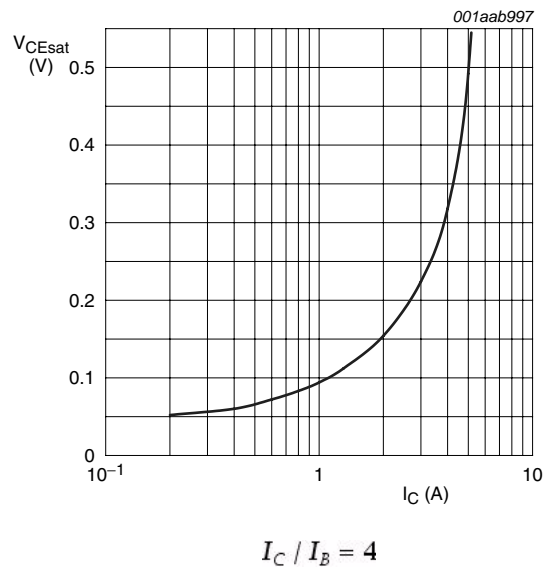
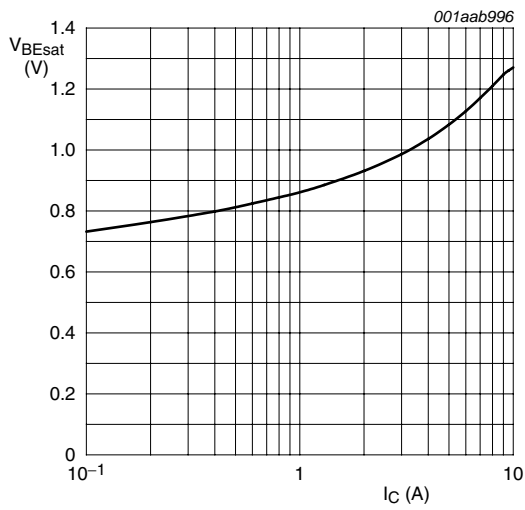
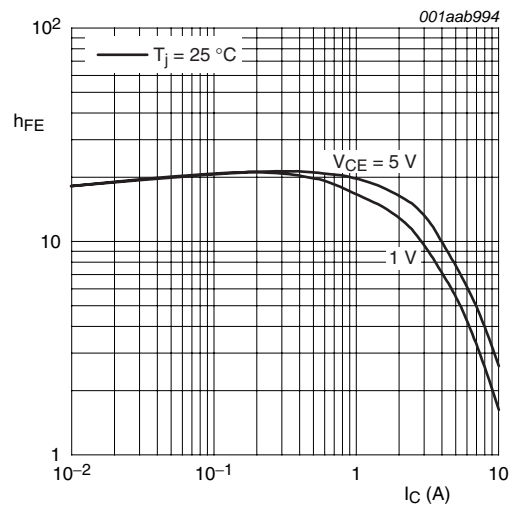


Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



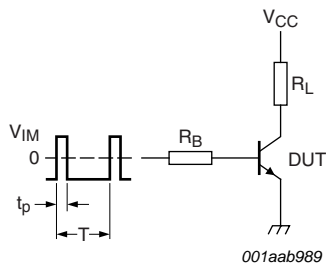
$I_C / I_B = 4$

Fig 10. Base-emitter saturation voltage as a function of collector current; typical values



$I_C / I_B = 4$

Fig 11. DC current gain as a function of collector current; typical values



$V_{IM} = -6 \text{ to } +8 \text{ V}; V_{CC} = 250 \text{ V}; t_p = 20 \mu\text{s}; \delta = \frac{t_p}{T} = 0.01$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 12. Test circuit for resistive load switching

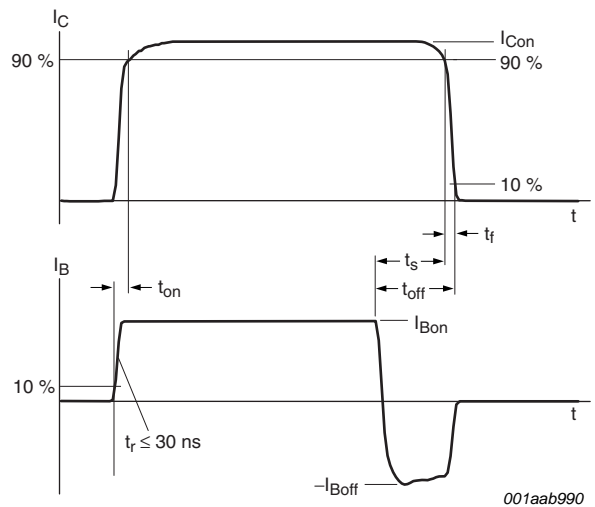
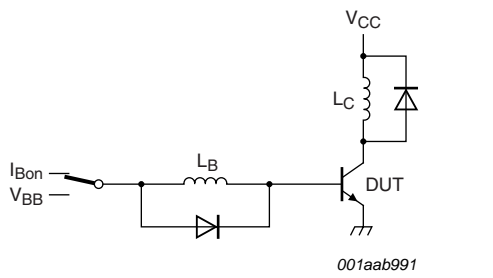


Fig 13. Switching times waveforms for resistive load



$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\ \mu\text{H}; L_B = 1\ \mu\text{H}$

Fig 14. Test circuit for inductive load switching

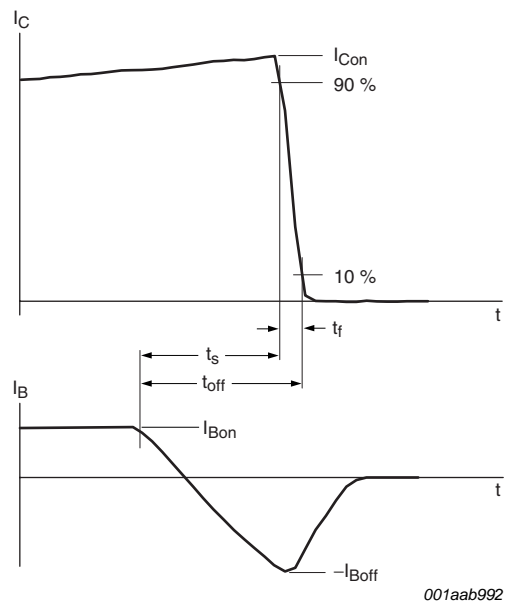


Fig 15. Switching times waveforms for inductive load

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

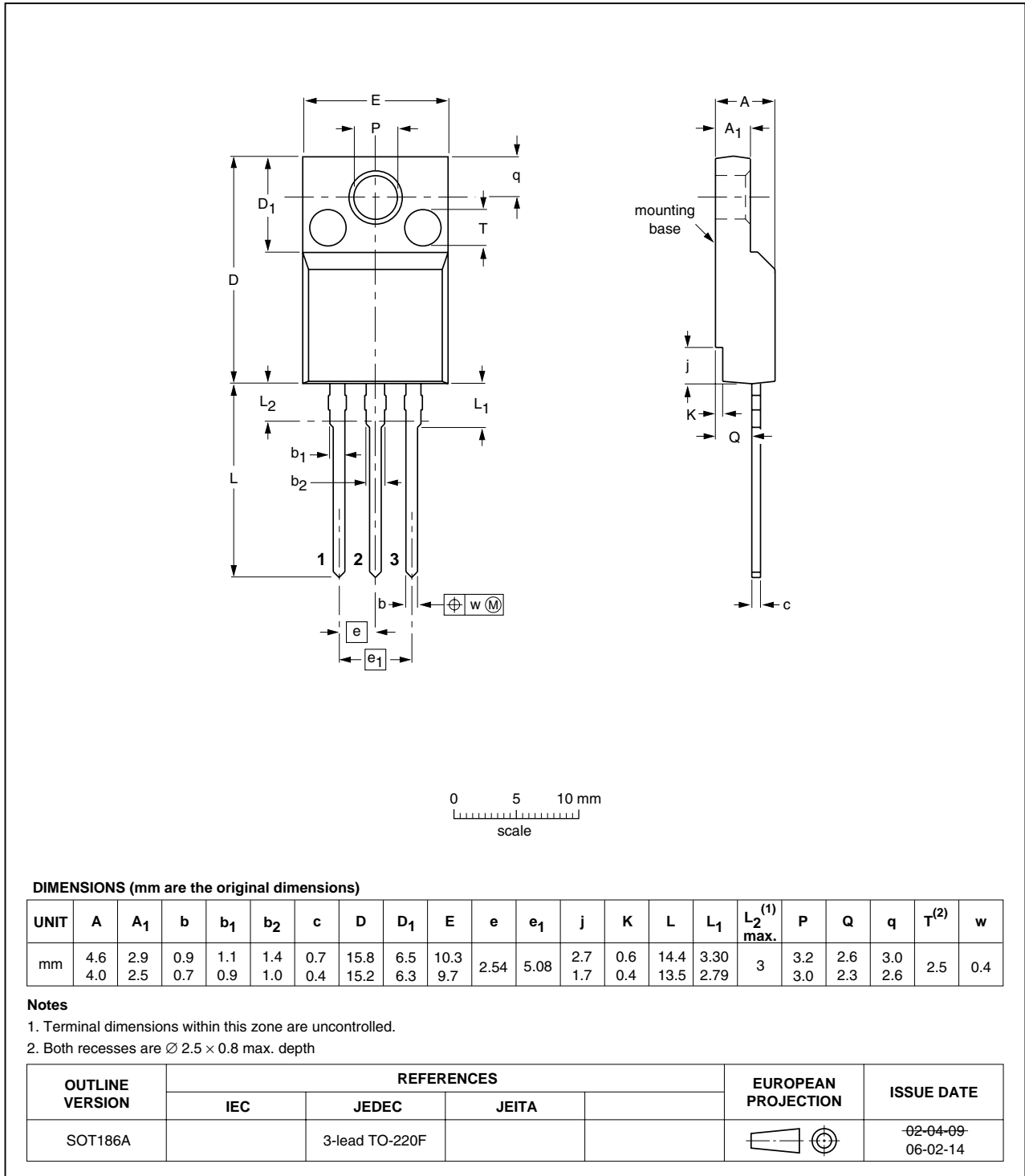


Fig 16. Package outline SOT186A (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJD203AX v.1	20100927	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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